

# DIGITRON SEMICONDUCTORS

FJT1100, FJT1101

ULTRA LOW LEAKAGE DIODES

$I_R = 1.0 \text{ pA (max) @ } 5V$  (FJT1100)

$BV = 20 \text{ V (min) (FJT1101)}$

## MAXIMUM RATINGS

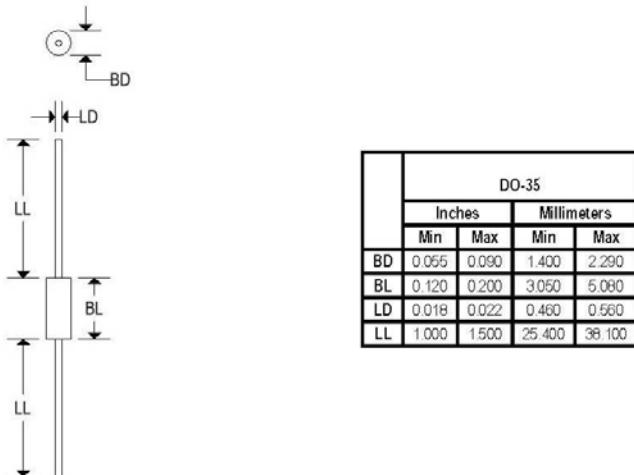
Characteristics	Value
Storage temperature range	-55° to +200°C
Maximum junction operating temperature	+175°C
Lead temperature	+260°C
Power dissipation	
Maximum total power dissipation at 25°C ambient	250 mW
Linear power derating factor (from 25°C)	1.67 mW/°C
Working inverse voltage	
FJT1100	25V
FJT1101	15V
Continuous forward current	150 mA

## ELECTRICAL CHARACTERISTICS (25°C ambient temperature unless otherwise noted)

Symbol	Characteristics	Min	Max	Units	Test Conditions
BV	Breakdown voltage	30		V	$I_R = 5.0\mu A$
		20			
$I_R$	Reverse current			pA	$V_R = 5.0V$ $V_R = 15V$ $V_R = 5.0V$ $V_R = 15V$
		FJT1100	1.0		
		FJT1101	10		
			5.0		
			15		
$V_F$	Forward voltage			V	$I_F = 50mA$
		FJT1100	1.05		
		FJT1101	1.10		
C	Capacitance			pF	$V_R = 0, f = 1MHz$
		FJT1100	1.5		
		FJT1101	1.8		

## MECHANICAL CHARACTERISTICS

Case	DO-35
Marking	Body painted, alpha-numeric
Polarity	Cathode band



Available Non-RoHS (standard) or RoHS compliant (add PBF suffix).

Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.